



# DCR890F65

# **Phase Control Thyristor**

Replaces DS5924-3 DS5924-4 July 2020 (LN40120)

### **FEATURES**

- Double Side Cooling
- High Surge Capability

### **APPLICATIONS**

- Medium Voltage Soft Starts
- High Voltage Power Supplies
- Static Switches

## **VOLTAGE RATINGS**

C,
nA,
)ms
VC
n )!

Lower voltage grades available.

### **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

### DCR890F65

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

### **KEY PARAMETERS**

<b>V</b> DRM	6500V
I <sub>T(AV)</sub>	894A
Ітѕм	12000A
dV/dt*	1500V/µs
dl/dt	200A/μs

<sup>\*</sup> Higher dV/dt selections are available

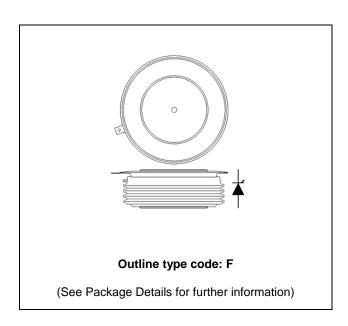


Fig. 1 Package outline

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<sup>\*6200</sup>V @ -40°C, 6500V @ 0°C



# **CURRENT RATINGS**

# T<sub>case</sub> = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
İT(AV)	Mean on-state current	Half wave resistive load	894	А
It(RMS)	RMS value	-	1404	А
lτ	Continuous (direct) on-state current	-	1371	А

# **SURGE RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, Tcase = 125°C	12.0	kA
l²t	I <sup>2</sup> t for fusing	V <sub>R</sub> = 0	0.72	MA <sup>2</sup> s

# THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions			Max.	Units
		Double side cooled	DC	-	0.0184	°C/W
Rth(j-c)	Thermal resistance - junction to case	Cinale side socied	Anode DC	-	0.0333	°C/W
		Single side cooled	Cathode DC	-	0.0418	°C/W
D		Clamping force 23kN	Double side	-	0.004	°C/W
Rth(c-h)	Thermal resistance - case to heatsink	(with mounting compound)	Single side	-	0.008	°C/W
Tvj	Virtual junction temperature	Blocking Vdrm / Vrrm		-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Clamping force			20	25	kN

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# **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Condition	ıs	Min.	Max.	Units
IRRM/IDRM	Peak reverse and off-state current	At VRRM/VDRM, Tcase = 125°C	;	-	200	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V <sub>DRM</sub> , T <sub>j</sub> = 125°C, ga	ate open	-	1500	V/µs
		From 67% VDRM to 2x IT(AV)	Repetitive 50Hz	-	100	A/µs
dl/dt	Rate of rise of on-state current	Gate source 30V, 10Ω	Non-repetitive	-	200	A/µs
		tr < 0.5µs, Tj = 125°C				
V====	Threshold voltage - Low level	300A to 900A at Tcase = 125°C			1.0	V
<b>V</b> т(то)	Threshold voltage - High level	900A to 3500A at Tcase = 12	25°C	-	1.1847	V
_	On-state slope resistance - low level	300A to 900A at Tcase = 12	-	1.1429	mΩ	
<b>r</b> T	On-state slope resistance - High level	900A to 3500A at Tcase = 12	-	0.9472	mΩ	
tgd	Delay time	$V_D = 67\% \ V_{DRM}$ , gate source 30V, $10\Omega$		-	3	μs
		tr = 0.5µs, Tj = 25°C				
tq	Turn-off time	$T_{j} = 125^{\circ}C$ , $I_{peak} = 1000A$ , $t_{p} = 1000\mu s$ , $V_{R} = 100V$ , $dI/dt = 5A/\mu s$ , $dV_{DR}/dt = 20V/\mu s$ linear to 2500V		600	1000	μs
Qs	Stored charge	Iτ = 1000A, tp = 1000μs, Tj = 125°C,		2500	4000	μC
<b>I</b> RR	Reverse recovery current	$dI/dt = 5A/\mu s$ , VR peak = 100V		90	120	А
<b>I</b> L	Latching current	Tj = 25°C, VD = 5V		-	3	Α
Ін	Holding current	Tj = 25°C, Rg-κ = ∞, Iτм = 500A, Iτ = 5A		-	300	mA

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## **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter Test Conditions		Max.	Units
<b>V</b> GT	Gate trigger voltage	VDRM = 5V, Tcase = 25°C	1.5	V
<b>V</b> GD	Gate non-trigger voltage	At 50% VDRM, Tcase = 125°C	0.4	V
lgт	Gate trigger current	VDRM = 5V, Tcase = 25°C	350	mA
Igp	Gate non-trigger current	At 50% VDRM, Tcase = 125°C	10	mA

## **CURVES**

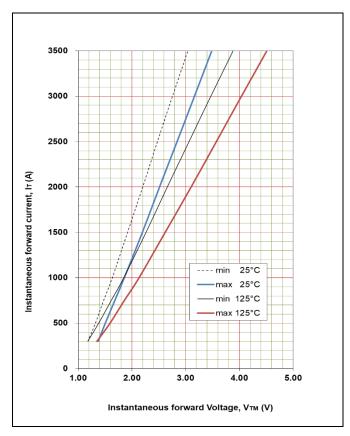


Fig. 2 Maximum & minimum on state characteristics

# **VTM EQUATION**

 $V_{TM} = A + B.In(I_T) + C.I_T + D.\sqrt{I_T}$ 

Where A = 0.874878

B = 0.001945

C = 0.000808

D = 0.013372

These values are valid for  $T_j = 125$ °C for  $I_T 300$ A to 3500A

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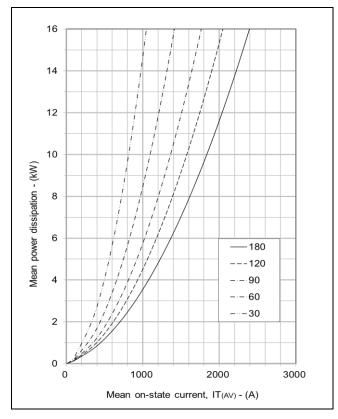


Fig. 3 On-state power dissipation - sine wave

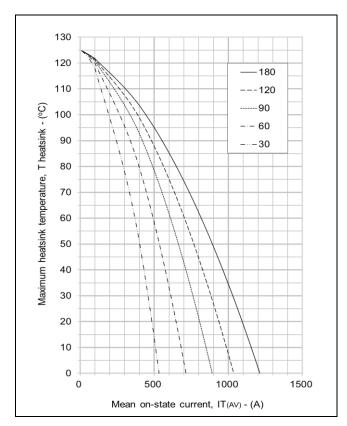


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

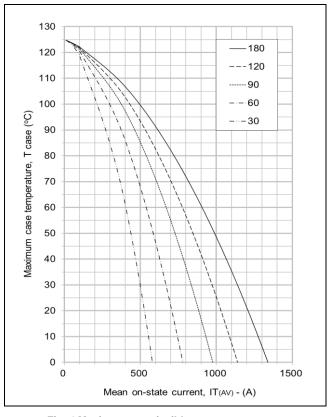


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

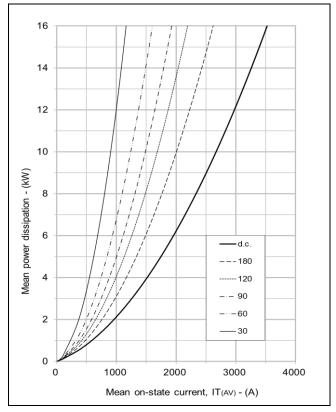


Fig. 6 On-state power dissipation - rectangular wave

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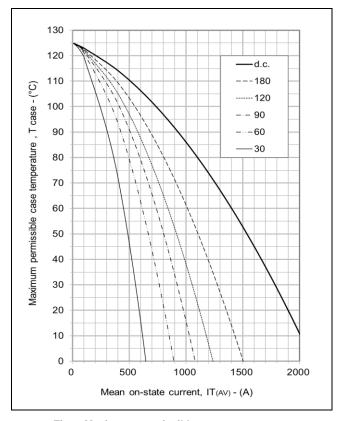
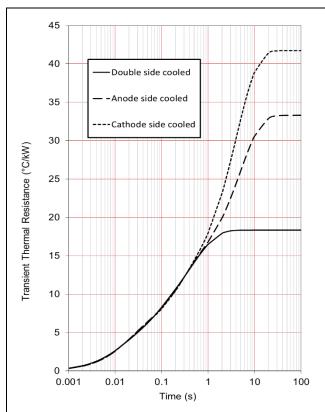


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



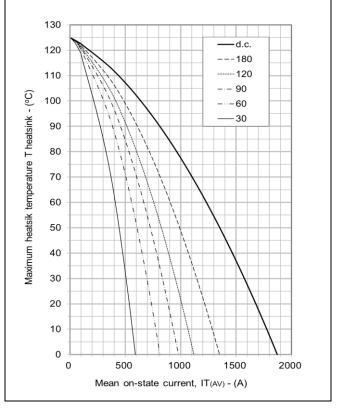


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	7.5608	4.0772	3.8420	2.8671
cooled	Ti(s)	0.6877	0.2537	0.0614	0.0101
Anode side	Ri(°C/kW)	11.5564	8.5810	4.7942	8.3643
cooled	Ti(s)	4.2216	6.0269	0.0166	0.2255
Cathode side	Ri(°C/kW)	6.7211	4.6219	15.5387	14.8631
cooled	Ti(s)	0.1910	0.0158	5.0011	3.3169

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

 $\Delta R_{\text{th(j-c)}}$  Conduction

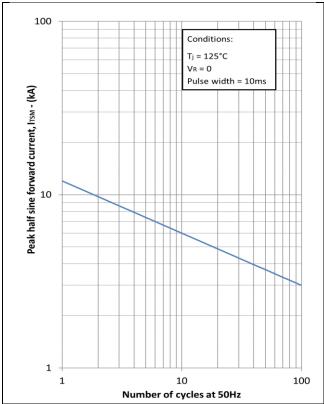
Tables show the increments of thermal resistance R  $_{\text{th(j-c)}}$  when the device operates at conduction angles other than d.c.

						_				
	Double side cooling			Anode Side Cooling			Cathode Sided Cooli		d Cooling	
	$\Delta Z_{th}(z)$			ΔΖ	$\Delta Z_{th}(z)$		$\Delta Z_{th}(z)$		<sub>h</sub> (z)	
θ°	sine.	rect.	6°	sine.	rect.		θ°	sine.	rect.	
180	3.19	2.14	180	2.97	203	1	180	295	2.02	
120	3.72	3.10	120	3.43	289	1	120	3.40	2.87	
90	4.29	3.64	90	3.92	3.36		90	3.88	3.34	
60	4.81	4.23	60	4.36	3.87		60	4.31	3.84	
30	5.22	4.88	30	4.69	4.41		30	4.64	4.37	
15	5.40	5.22	15	4.84	4.70		15	4.79	4.65	

Fig. 9 Maximum (limit) transient thermal impedance - junction to case (degC/kW)

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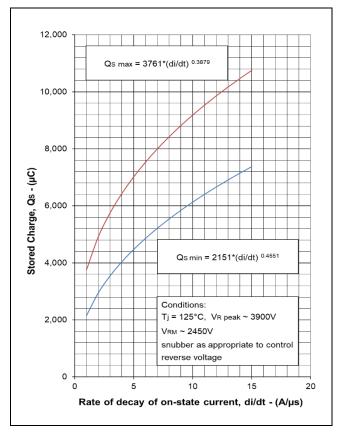


Fig. 12 Stored charge

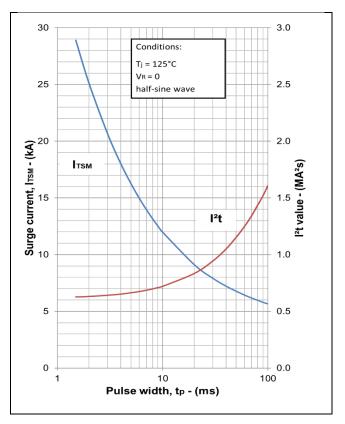


Fig. 11 Single-cycle surge current

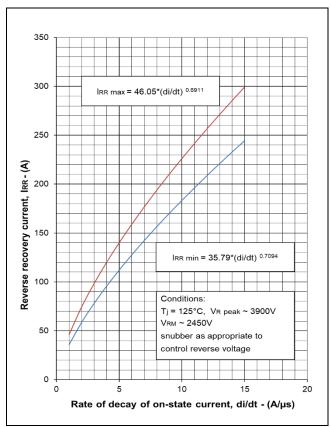


Fig. 13 Reverse recovery current

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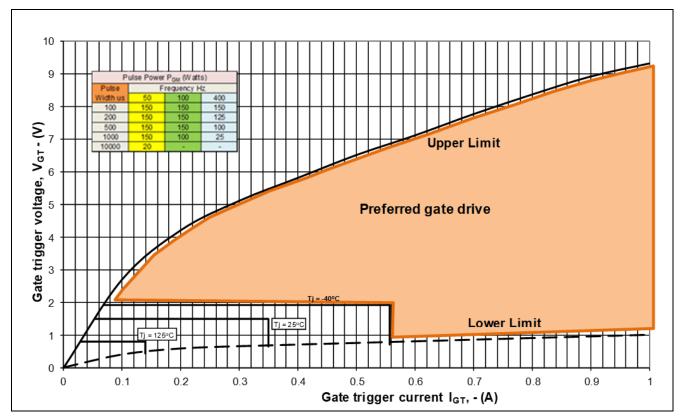


Fig. 14 Gate characteristics

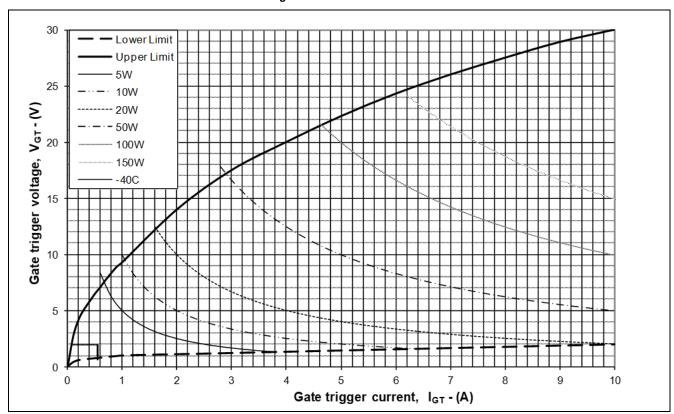


Fig. 15 Gate characteristics

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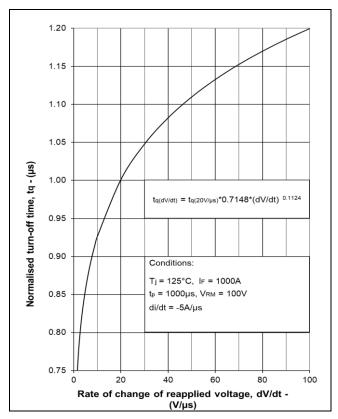


Fig. 16 Turn-off time

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## **PACKAGE DETAILS**

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

## DO NOT SCALE

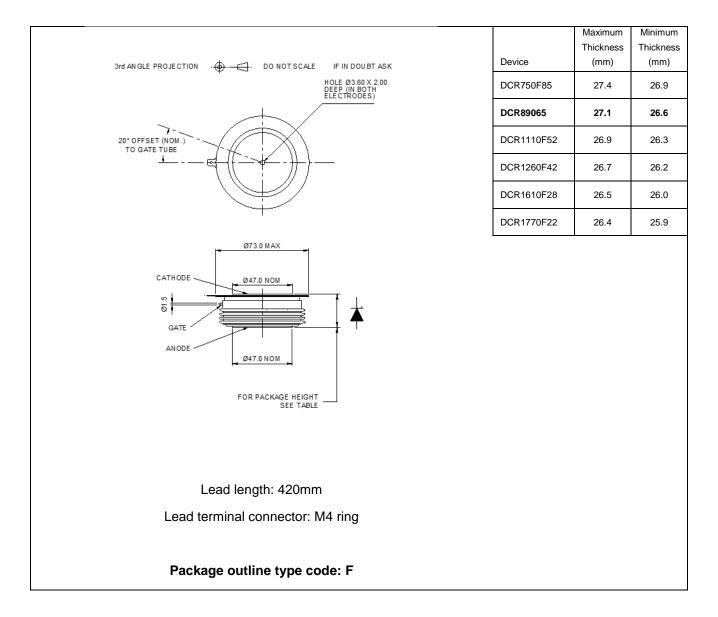


Fig. 17 Package outline

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